

CMOS µP-Compatible 12-Bit DAC

AD7542

FEATURES

Resolution: 12 Bits

Nonlinearity: ±1/2LSB T_{min} to T_{max} Low Gain Drift: 2ppm/°C typ, 5ppm/°C max

Microprocessor Compatible Full 4-Quadrant Multiplication

Fast Interface Timing

Low Power Dissipation: 40mW max

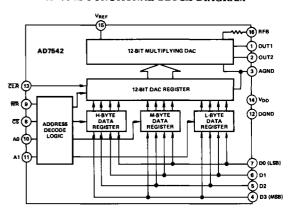
Low Cost

Small Size: 16-Pin DIP and 20 Terminal Surface Mount

Packages

Latch Free (Protection Schottky Not Required)

AD7542 FUNCTIONAL BLOCK DIAGRAM



GENERAL DESCRIPTION

The AD7542 is a precision 12-bit CMOS multiplying DAC designed for direct interface to 4- or 8-bit microprocessors.

The functional diagram shows the AD7542 to consist of three 4-bit data registers, a 12-bit DAC register, address decoding logic and a 12-bit CMOS multiplying DAC. Data is loaded into the data registers in three 4-bit bytes, and subsequently transferred to the 12-bit DAC register. All data loading or data transfer operations are identical to the WRITE cycle of a

static RAM. A clear input allows the DAC register to be easily reset to all zeros when powering up the device.

The AD7542 is manufactured using an advanced thin-film on monolithic CMOS fabrication process. Multiplying capability, low power dissipation, +5V operation, small size (16-pin DIP and 20 terminal surface mount packages) and easy μ P interface make the AD7542 ideal for many instrumentation, industrial control and avionics applications.

ORDERING INFORMATION1

		Temperature Range and Package Options ^{2,3}			
Relative	Gain	Commercial	Industrial	Extended	
Accuracy	Error	(Plastic)	(Ceramic)	(Ceramic)	
(T _{min} to T _{max})	+25°C	0 to +70°C	-25°C to +85°C	-55°C to +125°C	
±1LSB	±3LSB	AD7542JN	AD7542AD	AD7542SD	
±1LSB	±3LSB	AD7542JP	AD7542AE	AD7542SE	
±1/2LSB	±3LSB	AD7542KN	AD7542BD	AD7542TD	
±1/2LSB	±3LSB	AD7542KP	AD7542BE	AD7542TE	
±1/2LSB	±1LSB	AD7542GKN	AD7542GBD	AD7542GTD	
±1/2LSB	±1LSB	AD7542GKP	AD7542GBE	AD7542GTE	

NOTES

¹To order MIL-STD-883 Class B processed parts, add/883B to part number.

²Package Designation: Plastic DIP (N-16); Plastic Leaded Chip Carrier

(PLCC) (P-20A); Ceramic DIP (D-16); Leadless Ceramic Chip Carrier (LCCC) (E-20A).

³See Section 14 for package outline information.

$\textbf{SPECIFICATIONS} \ \, (\textbf{V}_{\text{DO}} = +5 \textbf{V}, \textbf{V}_{\text{REF}} = +10 \textbf{V}, \textbf{V}_{\text{OUT1}} = \textbf{V}_{\text{OUT2}} = 0 \textbf{V} \ \, \text{unless otherwise noted})$

Parameter	Limit At T _A = +25°C	Limit At ¹ T _A = 0, +70°C, -25°C & +85°C	Limit At ¹ T _A = -55°C & +125°C	Units	Conditions/Comments
ACCURACY					
Resolution	12	12	12	Bits	
Relative Accuracy ²	12	12	12	DIUS	
	±1	±1	±1	, cn	
J, A, S Versions	±1/2	±1/2	±1/2	LSB max	
K, B, T Versions	±1/2 ±1/2	±1/2 ±1/2	±1/2	LSB max	
GK, GB, GT Versions ~	±1/2	11/2	11/2	LSB max	
Differential Nonlinearity ²		l	l		491
J, A, S Versions	±1	±1	±1	LSB max	All grades are guaranteed monotonic
K, B, T Versions	±1	±1	±1	LSB max	T _{min} to T _{max}
GK, GB, GT Versions —	±ι	±1	±1	LSB max	
Gain Error ²		l			
J, K, A, B, S, T	±3	±4	±4	LSB max	Using internal RFB only (gain error can be
GK, GB, GT	±1	±1	±2	LSB max	trimmed to zero using circuits of Figure 4 & 5
Gain Temperature Coefficient					
∆Gain/∆Temperature	5	5	5	ppm/°C max	Typical value is 2ppm/°C
Power Supply Rejection		1 -	-	pp C	Typical value is appril
ΔGain/ΔV _{DD}	0.005	0.01	0.01	% per % max	V _{DD} = +4.75V to +5.25V
Output Leakage Current	0.007	1 0.02	0.01	wher willer	TDD = 14.757 to 45.257
	10	10	200	nA max	DAC Register loaded with all 0s
OUTI	10	10	200	nA max	DAC Register loaded with all 1s
lout2	10	10	200	na max	DAC Register toaded with all 1s
DYNAMIC PERFORMANCE					
Current Settling Time ³	2.0	2.0	2.0	μs max	To 1/2LSB, OUT1 load = 100Ω . DAC output
Carrent Setting Tane	1	•••	~."	μ3α	measured from falling edge of WR.
Multiplying Feedthrough Error ³	2.5	2.5	2.5	mV p-p max	V _{REF} = ±10V, 10kHz sine wave
	2.3	2.3	2.0	штүрүшж	VREF - 2104, TORTIZ SILIE WAVE
REFERENCE INPUT		l			
Input Resistance	8/15/25	8/15/25	8/15/25	kΩ min/typ/max	
ANALOG OUTPUTS					
Output Capacitance					
Çουτι [‡]	75	75	75	pF max	DAC register loaded to 0000 0000 0000
COUT13	260	260	260	pF max	DAC register loaded to 1111 1111 1111
COUT23	75	75	75	pF max	DAC register loaded to 1111 1111 1111
C _{OUT2} 3	260	260	260	pf max	DAC register loaded to 0000 0000 0000
			<u> </u>		
LOGIC INPUTS		l			
V _{INH} (Logic HIGH Voltage)	+2.4	+2.4	+2.4	V min	
V _{INL} (Logic LOW Voltage)	+0.8	+0.8	+0.8	V max	
I _{IN} *	1	1	1	μA max	V _{IN} = 0V or V _{DD}
C _{IN} (Input Capacitance) ³	8	8	8	pF max	
Input Coding	12-Bit Un	ipolar Binary or 12-I	Bit Offset	-	
	Binary (Se	e Figures 4 and 5). I	Data is		
	Loaded in	to Data Registers in	4-Bit Bytes.		
					
SWITCHING CHARACTERISTICS ⁵	(See Fig				
twr	80	120	160	ns min	twR: WRITE pulse width
t _{AWH}	0	10	10	ns min	tAWH: Address-to-WRITE hold time
t _{CWH}	0	10	10	ns min	tCWH: Chip select-to-WRITE hold time
^t CLR	200	200	250	ns min	tCLR: Minimum CLEAR pulse width
^t cws	10	20	20	ns min	t _{CWS} : Chip select-to-WRITE setup time
t _{AWS}	40	40	40	ns min	tAWS: Address valid-to-WRITE setup time
t _{DS}	60	100	100	ns min	t _{DS} : Data setup time
t _{DH}	10	10	10	ns min	tDH: Data hold time
POWER SUPPLY					
V _{DD} (Supply Voltage)	۱	٠. ا	١.,٠	v	+5% for englished performance
	+5	+5	+5	1 •	±5% for specified performance
I _{DD} (Supply Current)	2.5	2.5	2.5	mA max	Digital Inputs = V _{INH} or V _{INL}

NOTES

Temperature Ranges as follows: J, K, GK versions; 0 to +70°C
A, B, GB versions; -25°C to +85°C
S, T, GT versions; -55°C to +125°C

³ See definitions on next page.
³ Guaranteed but not tested.
⁴ Logic inputs are MOS gates. Typical input current (+25°C) is less than 1nA.
⁵ Sample tested at +25°C to ensure compliance.

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS*

 $(T_A = +25^{\circ}C \text{ unless otherwise noted})$

(1A) 13 (amous other wise notice)	To +70°C 670mW
V_{DD} to AGND	Derates above +70°C by 8.3mW/°C
V_{DD} to DGND	Ceramic
AGND to DGND V_{DD} +0.3V	To +75°C
DGND to AGND , V_{DD} +0.3V	Derates above +75°C by 6mW/°C
Digital Input Voltage to GND $-0.3V$, $V_{\rm DD}$ $+0.3V$	Operating Temperature Range
V_{OUT1} , V_{OUT2} to AGND0.3V, V_{DD} +0.3V	Commercial (J, K, GK Versions) 0 to +70°C
V_{REF} to AGND	Industrial (A, B, GB Versions)25°C to +85°C
V_{RFB} to AGND	Extended (S, T, GT Versions)55°C to +125°C
	Storage Temperature65°C to +150°C
	Lead Temperature (Soldering, 10secs) + 300°C

Power Dissipation (Package)

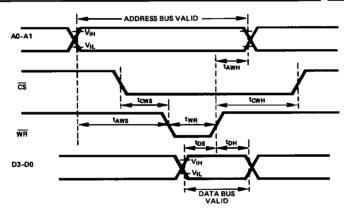
Plastic

*COMMENTS: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION

ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are removed.

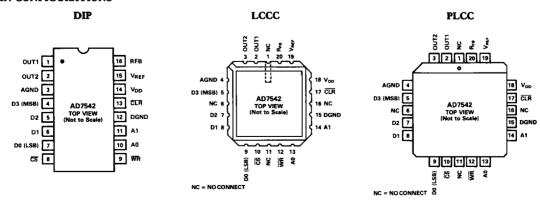




NOTE: TIMING MEASUREMENT REFERENCE LEVEL IS $\frac{V_{IH} + V_{IL}}{2}$

Figure 1. AD7542 Timing Diagram

PIN CONFIGURATIONS



TERMINOLOGY

RELATIVE ACCURACY

Relative accuracy or endpoint nonlinearity is a measure of the maximum deviation from a straight line passing through the endpoints of the DAC transfer function. It is measured after adjusting for zero and full scale and is expressed in % or ppm of full scale range or (sub) multiples of 1LSB.

DIFFERENTIAL NONLINEARITY

Differential nonlinearity is the difference between the measured change and the ideal 1LSB change between any two adjacent codes. A specified differential nonlinearity of ±1LSB max over the operating temperature range insures monotonicity.

GAIN ERROR

Gain is defined as the ratio of the DAC's Full Scale output to its reference input voltage. An *ideal* AD7542 would exhibit a gain of -4095/4096. Gain error is adjustable using external trims as shown in Figures 4 and 5.

OUTPUT LEAKAGE CURRENT

Current which appears at OUT1 with the DAC register loaded to all 0s or at OUT2 with the DAC register loaded to all 1s.

MULTIPLYING FEEDTHROUGH ERROR

AC error due to capacitive feedthrough from V_{REF} terminal to OUT1 with DAC register loaded to all 0s.

PIN	MNEMONIC	FUNCTION
1	OUT1	DAC current output bus. Normally terminated at op amp virtual ground
2	OUT2	DAC current output bus. Normally terminated at ground
3	AGND	Analog Ground
4	D3	Data Input (MSB)
5	D2	Data Input
6	D1	Data Input
7	D0	Data Input (LSB)
8	<u>cs</u>	Chip Select Input
9	WR	WRITE Input
10	A0	Address Bus Input
11	A1	Address Bus Input
12	DGND	Digital Ground
13	CLR	Clear Input
14	V_{DD}	+5V Supply Input
15	V_{REF}	Reference Input
16	R _{FB}	DAC Feedback Resistor

Table 1. Pin Function Description (DIP Pin Numbers)

Analog Circuit Description

GENERAL CIRCUIT INFORMATION

The AD7542, a 12-bit multiplying D/A converter, consists of a highly stable thin film R-2R ladder and twelve N-channel current switches on a monolithic chip. Most applications require the addition of only an output operational amplifier and a voltage or current reference.

The simplified D/A circuit is shown in Figure 2. An inverted R-2R ladder structure is used—that is, the binarily weighted currents are switched between the OUT1 and OUT2 bus lines, thus maintaining a constant current in each ladder leg independent of the switch state.

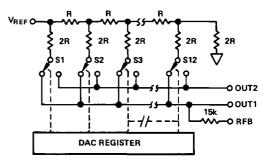


Figure 2. D/A Simplified Circuit Diagram

One of the current switches is shown in Figure 3. The input resistance at V_{REF} (Figure 2) is always equal to R_{LDR} (R_{LDR} is the R/2R ladder characteristic resistance and is equal to value "R"). Since R_{IN} at the V_{REF} pin is constant, the reference terminal can be driven by a reference voltage or a reference current, ac or dc, of positive or negative polarity. (If a current source is used, a low temperature coefficient R_{FB} is recommended to define scale factor.)

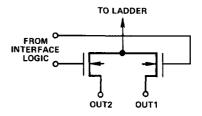


Figure 3. N-Channel Current Steering Switch

Applying the AD7542

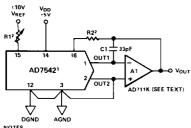
UNIPOLAR BINARY OPERATION (2-QUADRANT MULTIPLICATION)

Figure 4 shows the analog circuit connections required for unipolar binary (2-quadrant multiplication) operation. The logic inputs are omitted for clarity. With a dc reference voltage or current (positive or negative polarity) applied at V_{REF}, the circuit is a unipolar D/A converter. With an ac reference voltage or current the circuit provides 2-quadrant multiplication (digitally controlled attenuation). The input/output relationship is shown in Table II.

R1 provides full scale trim capability [i.e.—load the DAC register to 1111 1111 1111, adjust R1 for $V_{OUT} = -V_{REF}$ (4095/4096)]. Alternatively, Full Scale can be adjusted by omitting R1 and R2 and trimming the reference voltage magnitude.

C1 phase compensation (10 to 33pF) may be required for stability when using high speed amplifiers. (C1 is used to cancel the pole formed by the DAC internal feedback resistance and output capacitance at OUT1).

Amplifier A1 should be selected or trimmed to provide $V_{OS} \le 10\%$ of the voltage resolution at V_{OUT} . Additionally, the amplifier should exhibit a bias current which is low over the temperature range of interest (bias current causes output offset at V_{OUT} equal to I_B times the DAC feedback resistance, nominally $15 \mathrm{k}\Omega$). The AD711K is a high-speed implanted FET-input op amp with low, factory-trimmed V_{OS} .



NOTES
1 LOGIC INPUTS OMITTED FOR CLARITY, DIP PIN NUMBERS SHOWN 2 SEE APPLICATION HINT NO 4

Figure 4. Unipolar Binary Operation (2-Quadrant Multiplication)

BINARY N DAC REC MSB		ANALOG OUTPUT, V _{OUT}
1111 11	11 1111	$-V_{REF}\left(\frac{4095}{4096}\right)$
1000 000	00 0000	$-V_{REF}(\frac{2048}{4096}) = -1/2 V_{REF}$
0000 000	00 0001	$-V_{REF}\left(\frac{1}{4096}\right)$
0000 000	00 0000	ov

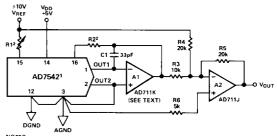
Table II. Unipolar Binary Code Table for Circuit of Figure 4

BIPOLAR OPERATION (4-QUADRANT MULTIPLICATION)

Figure 5 and Table III illustrate the circuitry and code relationship for bipolar operation. With a dc reference (positive or negative polarity) the circuit provides offset binary operation. With an ac reference, the circuit provides full 4-quadrant multiplication.

With the DAC register loaded to 1000 0000 0000, adjust R1 for V_{OUT} = 0V (alternatively, one can omit R1 and R2 and adjust the ratio of R3 to R4 for V_{OUT} = 0V). Full scale trimming can be accomplished by adjusting the amplitude of V_{REF} or by varying the value of R5.

As in unipolar operation, A1 must be chosen for low V_{OS} and low I_B . R3, R4 and R5 must be selected for matching and tracking. Mismatch of R3 to R4 causes both offset and Full Scale error. Mismatch of R5 to R4 or R3 causes Full Scale error. C1 phase compensation (10pF to 25pF) may be required for stability.



NOTES
1 LOGIC INPUTS OMITTED FOR CLARITY, DIP PIN NUMBERS SHOWN
2 SEE APPLICATION HINT NO 4

Figure 5. Bipolar Operation (4-Quadrant Multiplication)

BINARY N	IUMBER IN SISTER	ANALOG OUTPUT, V _{OUT}
MSB	LSB	
1111 11	11 1111	$+V_{REF}\left(\frac{2047}{2048}\right)$
1000 00	000 0001	$+V_{REF}\left(\frac{1}{2048}\right)$
1000 00	000 0000	ov
0111 11	11 1111	$-V_{REF}\left(\frac{1}{2048}\right)$
0000 00	000 0000	$-V_{REF}\left(\frac{2048}{2048}\right)$

Table III. Bipolar Code Table for Offset Binary Circuit of Figure 5

INTERFACE LOGIC INTERFACE LOGIC INFORMATION

The AD7542 is designed to interface as a memory-mapped output device.

A typical system configuration is shown in Figure 6. \overline{CS} is the decoded device address, and is derived by decoding the three higher order address bits. A0 and A1 is the AD7542 operation address, and is decoded internally in the AD7542 to point to the desired loading operation (i.e., load high byte, middle byte, low byte or DAC register). Table IV shows the AD7542 truth table.

All data loading operations are identical to the write cycle of a RAM as shown in Figure 1.

Additionally, the CLR input allows the AD7542 DAC register to be cleared asynchronously to 0000 0000 0000. When operating the AD7542 in a unipolar mode (Figure 4), a CLEAR causes the DAC output to assume 0V. In the bipolar mode (Figure 5), a CLEAR causes the DAC output to go to -V_{REF}.

In summary:

- The AD7542 DAC register can be asynchronously cleared with the CLR input.
- 2. Each AD7542 requires 4 locations in memory.
- 3. Performing any of the four basic loading operations (i.e. load low byte data register, middle byte data register, high byte data register or 12-bit DAC register) is accomplished by executing a memory WRITE operation to the applicable address location for the required DAC operation.

AD7542 Control Inputs				its		
A ₁	A ₀	cs	₩R	CLR	AD7542 Operation	
х	х	х	х	0	Resets DAC 12-Bit Register to Code 0000 0000 0000	
х	х	1	х	1	No Operation Device Not Selected	
0	0	0	£	1	Load LOW Byte ⁵ Data Register On Edge As Shown	Load
0	1	0	Ŧ	1	Load MIDDLE Byte ⁵ Data Register On Edge As Shown	Applicable Data Register
1	0	0		1	Load HIGH Byte ⁵ Data Register On Edge As Shown	With Data At D ₀ - D ₃
1	1	0	ıı	1	Load 12-Bit DAC Register With Data In LOW Byte, MIDDLE Byte & HIGH Byte Data Registers ⁶	

10	т	r	c	

¹ I indicates logic HIGH ² 0 indicates logic LOW *MSB → XXXX XXXX XXXX → LSB
high middle low byte byte

Table IV. AD7542 Truth Table

AD7542 INTERFACE TO MC6800

A typical 6800 system configuration is shown in Figure 6. Since the AD7542 contains four registers each AD7542 is assigned four locations in memory. A0 and A1 provides the operational addresses and are decoded internally to point to the desired register. Register loading is accomplished by executing a memory WRITE instruction to one of the four addresses. Table V gives a sample loading subroutine written in re-entrant form.

Choosing an arbitrary start address of PPQQ, locations PPQQ, PPQQ+1 and PPQQ+2 select the low, middle and high byte registers respectively while address PPQQ+3 selects the 12-bit DAC register. The 12-bit data to be passed to the subroutine is stored in locations XXYY and XXYY+1. The four most significant data bits are assumed to occupy the lower half of XXYY+1.

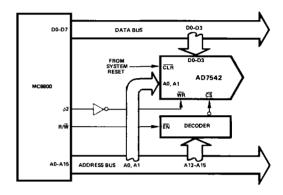


Figure 6. Interfacing the AD7542 to an MC6800 Microprocessor

	JSR	WWZZ	
WWZZ	PSH A		PUSH ACC. A ONTO STACK
	TPA		
	PSH A		PUSH CCR ONTO STACK
	LDA A	XXYY	
	STA A	PPQQ	LOAD LOW BYTE
	ROR A		
	STA A	PPQQ+1	LOAD MIDDLE BYTE
	LDA A	XXYY+1	
	STA A	PPQQ+2	LOAD HIGH BYTE
	STA A	PPQQ+3	LOAD DAC REGISTER
	PUL A		
	TAP		POP CCR FROM STACK
	PUL A		POP ACC. A FROM STACK
	RTS		RETURN TO MAIN PROGRAM

Table V. Sample Routine for AD7542-6800 Interface

AD7542 INTERFACE TO 8085

A typical 8085 system configuration is shown in Figure 7. The AD7542 \overline{CS} input is decoded from the three high order address lines A13-A15. The 8085 \overline{WR} output is directly connected to the \overline{WR} input of the AD7542. Table VI gives a sample loading subroutine written in re-entrant form. The 12-bit data to be passed to the subroutine is stored in locations XXYY and XXYY+1. The four most significant data bits are assumed to occupy the lower half of XXYY+1. As before, arbitrary addresses PPQQ to PPQQ+3 select the low byte, middle byte, high byte and DAC registers respectively.

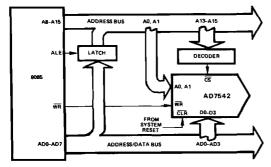


Figure 7. Interfacing the AD7542 to an 8085 Microprocessor

CALL	7542	
PUSH	PSW	PUSH REGISTER CONTENTS
PUSH	В	ONTO STACK
PUSH	н	
LXI	H, XXYY	
MOV	A, M	
STA	PPQQ	LOAD LOW BYTE
MVI	B, 04	
RAR		
DCR	В	
JNZ	LOOP	
STA	PPQQ+1	LOAD MIDDLE BYTE
INX	H	
MOV	A, M	
STA	PPQQ+2	LOAD HIGH BYTE
STA	PPQQ+3	LOAD DAC REGISTER
POP	Н	POP REGISTER CONTENTS
POP	В	FROM STACK
POP	PSW	
RET		RETURN TO MAIN PROGRAM
	PUSH PUSH PUSH LXI MOV STA MVI RAR DCR JNZ STA INX MOV STA STA POP POP	PUSH PSW PUSH B PUSH H LXI H, XXYY MOV A, M STA PPQQ MVI B, 04 RAR DCR B JNZ LOOP STA PPQQ+1 INX H MOV A, M STA PPQQ+2 STA PPQQ+3 POP H POP B POP PSW

Table VI. Sample Routine for AD7542-8085 Interface

APPLICATION HINTS

The AD7542 is a precision 12-bit multiplying DAC designed for system interface. To ensure system performance consistent with AD7542 specifications, careful attention must be given to the following points:

1. GENERAL GROUND MANAGEMENT: Voltage differences between the AD7542 AGND and DGND cause loss of accuracy (de voltage difference between the grounds introduces gain error. AC or transient voltages between the grounds cause noise injection into the analog output). The simplest method of ensuring that voltages at AGND and DGND are equal is to tie AGND and DGND together at the AD7542. In more complex systems where the AGND-DGND intertie is on the back-plane, it is recommended that diodes be connected back-to-back between the AD7542 AGND and DGND pins (1N914 or equivalent).

- 2. OUTPUT AMPLIFIER OFFSET: CMOS DACs exhibit a code-dependent output resistance which in turn causes a code-dependent amplifier noise gain. The effect is a non-linearity term at the amplifier output which depends on V_{OS} (V_{OS} is amplifier input offset voltage). This non-linearity term adds to the R/2R nonlinearity. To maintain specified operation, it is recommended that amplifier V_{OS} be no greater than 10% of the DAC's output resolution over the temperature range of interest [output resolution = V_{REF} (2^{-n}) where n is the number of bits exercised].
- 3. HIGH FREQUENCY CONSIDERATIONS: AD7542 output capacitance works in conjunction with the amplifier feedback resistance to add a pole to the open loop response. This not only reduces closed loop bandwidth, but can also cause ringing or oscillation if the spurious pole frequency is less than the amplifier's OdB crossover frequency. Stability can be restored by adding a phase compensation capacitor in parallel with the feedback resistor.
- 4. GAIN TEMPERATURE COEFFICIENTS: The gain temperature coefficient of the AD7542 has a maximum value of 5ppm/°C and a typical value of 2ppm/°C. This corresponds to gain shifts of 2,0LSBs and 0.82LSBs respectively over a 100°C temperature range. When trim resistors are used to adjust full-scale range as shown in Figures 4 and 5 the temperature coefficient of R1 and R2 should be taken into account. It may be shown that the additional gain temperature coefficients introduced by R1 and R2 may be approximately expressed as follows: —

Temperature Coefficient contribution due to R1 =
$$-\frac{R_1}{R_{1N}}$$
 ($\gamma_1 + 300$)

Temperature Coefficient contribution due to R2 = $+\frac{R_2}{R_{1N}}$ ($\gamma_2 + 300$)

Where γ_1 and γ_2 are the temperature coefficients in ppm/ $^\circ$ C of R1 and R2 respectively and R_{IN} is the DAC input resistance at the V_{REF} terminal (pin 2). For high quality wirewound resistors and trimming potentiometers γ is of the order of 50ppm/ $^\circ$ C. It will be seen that if R1 and R2 are small compared with R_{IN}, their contribution to gain temperature coefficient will also be small. For the standard AD7542 gain error specification of ± 3 LSBs it is recommended that R1 = 50Ω and R2 = 25Ω . With γ = 50 these values result in an overall maximum gain error temperature coefficient of:

$$5 + \frac{0.025}{8} (50 + 300) = 6 \text{ppm/}^{\circ} \text{C}$$

However, if the AD7542GTD is used which has a specified gain error of $\pm 1LSB$, then with $R1=10\Omega$ and $R2=5\Omega$ the overall maximum gain temperature coefficient is increased by only 0.25ppm/°C. Where possible R1 should be a select on test fixed resistor since the resulting gain temperature coefficient will be tighter in all cases. For further gain T.C. information refer to application note, "Gain Error and Gain Temperature Coefficients of CMOS Multiplying DACs", Publication Number E630–10–6/81 available from Analog Devices.

 For additional information on multiplying DACs refer to "CMOS DAC Application Guide," Publication Number G872a-15-4/86, available from Analog Devices.